

MATÉRIAUXCRYSTAL CHEMISTRY OF PEROVSKITE-LIKE LAYER-TYPE FERROELECTRICS

I. Ismailzade

▶ To cite this version:

I. Ismailzade. MATÉRIAUXCRYSTAL CHEMISTRY OF PEROVSKITE-LIKE LAYER-TYPE FERROELECTRICS. Journal de Physique Colloques, 1972, 33 (C2), pp.C2-237-C2-239. 10.1051/jphyscol:1972282. jpa-00215018

HAL Id: jpa-00215018 https://hal.science/jpa-00215018

Submitted on 4 Feb 2008

HAL is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers. L'archive ouverte pluridisciplinaire **HAL**, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d'enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.

CRYSTAL CHEMISTRY OF PEROVSKITE-LIKE LAYER-TYPE FERROELECTRICS

I. H. ISMAILZADE

The Institute of Theoretical Problems of Chemical Technology of the Academy of Sciences of the Azerbaijan S. S. R., Baku, U. S. S. R.

Résumé. — Le nombre *m* de couches monooctaédriques dans les empilements du type perovskite dépend de la valeur du facteur de tolérance *t*. Les critères limites, supérieur et inférieur, de formation de structures en couches sont $t_1 \simeq 0,87$ et $t_u \simeq 0,99$. Dans les couches $[Bi_2O_2]^{2+}$, seulement un des ions Bi^{3+} peut être remplacé, et seulement par un cation trivalent; cela conduit à accroître T_c . L'accroissement de *m*, dépendant de la polarisabilité des ions A et O^{2-} cause à la fois l'élévation et l'abaissement de T_c . Bi_2WO_6 est le premier ferroélectrique à une couche avec T_c 950 °C.

Les cristaux Bi_2NbO_5F et Bi_2TaO_5F sont aussi des cristaux ferroélectriques à une couche ayant respectivement pour T_c les valeurs 30 °C et 10 °C.

La chimie des cristaux ferroélectriques du type perovskite à couche a été considérablement étudiée, et les points principaux sont donnés dans la présente note.

Abstract. — The number of monooctahedral layers in the perovskite-like package *m* depends on the value of tolerance factor *t*. The lower and upper criteria of layer structure formation are $t_1 \approx 0.87$ and $t_u \approx 0.99$. In $[Bi_2O_2]^{2+}$ layers only one of the Bi³⁺ ions may be replaced, and only by trivalent cation; that leads to increasing of T_c . Depending upon the polarizability of A and O²-ions increasing of *m* causes both raising and lowering of T_c . Bi₂WO₆ is the first one-layer ferroelectric with $T_c \approx 950$ °C. Crystals Bi₂NbO₅F and Bi₂TaO₅F are also one-layer ferroelectrics with $T_c \approx 30$ °C and 10 °C.

Crystal chemistry of perovskite-like layer-type ferroelectrics has been considerably developed in [1]-[5] the main points of which are given in the present paper.

1. The general formula of layer-type ferroelectrics is A_{m-n+1} Bi_n B_m O_{3m+3} [1], where A are large cations occuping usually octahedral emptinesses in perovskite-like packages, B-small cations, m- is a number of monooctahedral layers in one perovskite-like unit (Fig. 1), n = 2 or 4.

In the earlier known layer-type ferroelectrics m was equal only to 2, 3, 4 and 5. In our work [2] it was shown that the value of m depends on geometry of ions packing in perovskite-like units-upon the magnitude of the tolerance factor t. It was established that the upper and lower criteria favorable for the formation of perovskite-like layer-type structure are $t_u \approx 0.99$ and $t_1 \approx 0.87$ in the interval of which structures can be formed theoretically with any number of monooctahedral layers in the perovskite-like package. Figure 2 shows the dependence of m upon t for

$$A = Ba^{2+}$$
, Pb^{2+} , Bi^{3+} , Sr^{2+} and Ca^{2+} .

For the system N ATiO₃-Bi₄Ti₃O₁₂ ($A = Pb^{2+}$, Sr²⁺, Ca²⁺) and N BiFeO₃-Bi₄Ti₃O₁₂ any number m is possible. In particular formation of the first eight-layer ferroelectric-anti-ferromagnetic Bi₅Bi₄-Ti₃Fe₅O₂₇, $T_c = 830$ °C [2], [3] confirms this conclusion.

In cases when cations A are different, the concept of an average ionic radius, and consequently the calculated factor t, is applicable if the sizes of these ions do not considerably differ. Otherwise in determining of the possibility of a layer structure formation it is necessary to bear in mind the values of the factor t, separatly calculated for each of A cations.

Satisfaction of the geometrical criteria (on the nominal charges of ions) is necessary but it is not always sufficient for formation of the layer-type structure. The electron configuration of ions in the unit cell and polarizability of the cations A and B play an important role. Apparently in some cases a considerable deviation of effective charge of ions from the nominal charges can stipulate the seeming deviation from the established criteria.

2. Possibility of formation of the $[Me_2O_2]$ layers predetermines building of the perovskite-like layer structure. In this connection investigation of the substitution of Bi³⁺ ions by another ions in the bismuth-oxygen layers is very important. According to Subbarao [4] and Popper *et al.* [5] Bi³⁺ ions in $[Bi_2O_2]^{2+}$ layers cannot be replaced without destroying the structure. Our investigation show that [3] in the bismuth-oxygen layer the only one of the two Bi³⁺ ions can be substituted, and only by trivalent cations. Such a replacement of ions sufficiently effects the value of the Curie temperature of a crystal, what we shall mention later on.

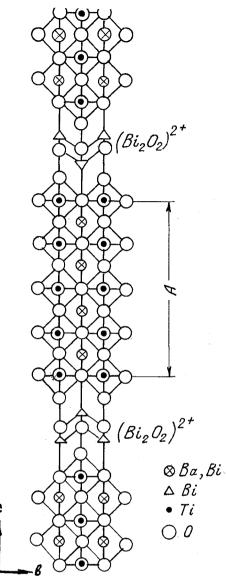


FIG. 1. — The unit cell of ferroelectric $Ba_2Bi_4Ti_5O_{18}$ projected on (100).

3. Earlier it was adopted that by the given A and Bcations with increasing of m the Curie temperature T_{e} of the layer-type ferroelectrics decreases. Recently we have shown [3] that in the general case increasing of m can lead to decreasing as well as to increasing of T_c of this type ferroelectrics. In comparison with the perovskite structure, perovskite-like packages differ by some surplus of oxygen ions and to the same degree by deficiency of cations A. With increasing of m surplus of O^{2-} and deficiency of A gradually are diminished and they strive for mutual compensation, that is the perovskite-like package approaches the perovskite unit. This in general should led to decreasing of T_{e} . However, so far as deficiency of cations A decreases, then character of the change of T_c will depend upon the magnitude of polarizability of A cations α_A as compared with polarizability of O^{2-} ion. At $\alpha_A < \alpha_0$ with increasing of m decreasing of T_c will occur.

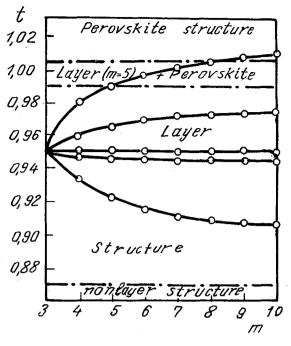


FIG. 2. — The dependence $m = \varphi(t)$.

However in case $\alpha_A > \alpha_0$ both increasing (when $A = Bi^{3+}$) and decreasing (when $A \neq Bi^{3+}$) of T_c take place. For example, the first occurs in the following case :

	m	<i>T</i> _c , ⁰C
		<u> </u>
BiBi ₄ Ti ₃ FeO ₁₅	4	750
Bi ₂ Bi ₄ Ti ₃ Fe ₂ O ₁₈	5	810
Bi ₅ Bi ₄ Ti ₃ Fe ₅ O ₂₇	8	830

Thus the T_c of layer-type ferroelectrics depend upon the nature of A (and B) cations, disposing in the perovskite-like units, and apparently in this the bismuth-oxygen layers at all events do not play a considerable role.

4. The Curie temperature of layer-type ferroelectrics to a great extent depends also upon the fact if the Acations are placed in the perovskite-like units or they enter into the bismuth-oxygen layers. In the last case Bi^{3+} ion which is replaced by cation A, passes to perovskite-like unit that should cause a considerable raising of T_c of crystal. By this, in particular, the equal values $T_c \approx 750 \text{ °C}$ of ferroelectrics $PrBi_4Ti_3FeO_{15}$ [7] and $BiBi_4Ti_3FeO_{15}$ [2] are explained. Thus, such a kind of increasing of T_c may be as an indicator of replacing of Bi^{3+} ions in the bismuth-oxygen layers.

For a given *B* cations the degree of broadening of the ferroelectric phase transition (the width of the dielectric constant peak) is in direct dependence on the size difference of *A* and Bi^{3+} ions. Because of this the peaks of ε are sharp if *A* ion enters only into the bismuth-oxygen layer (for example, in $PrBi_4Ti_3FeO_{15}$) and broadening if it is placed in the perovskite-like unit (as in $LaBi_4Ti_3FeO_{15}$, Fig. 3). Evidently, this result

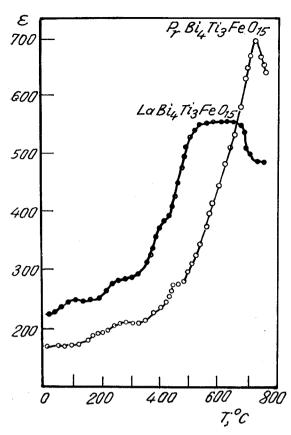


FIG. 3. — The dependence e(T) of PrBi₄Ti₃FeO₁₅ and LaBi₄Ti₃FeO₁₅.

also may serve as an evidence of replacement of Bi^{3+} ion in the bismuth-oxygen layer by A cation.

5. The chemical formula of possible one-layer perovskite-like layer-type ferroelectrics Bi_2BO_6 is obtained from the general formula at m = 1 and n = 2. However up to 1970 the existence of these ferroelectrics was unknown. For the first time on the basis of high temperature X-ray investigation [8] and a non-polar space group D_{2h}^{10} -Pccn [8] it was concluded

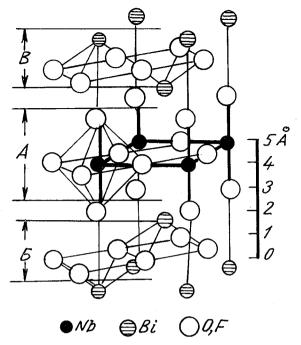


FIG. 4. — One half of the unit cell of Bi_2NbO_5F [11].

by us that, probably, bismuth-tungstat, Bi₂WO₆, was antiferroelectric with $T_c \approx 950 \text{ °C}$ [9]. However, recently for Bi_2WO_6 a polar group C_{2v}^{17} -B2cb was determined [10]. This allows us to contend that Bi₂WO₆ is the first discovered one-layer ferroelectric (may be ferrielectric) with $T_{\rm c} \approx 950$ °C. Other one-layer compounds Bi₂NbO₅F and Bi₂TaO₅F were synthetized and structurally studied in [11] and C_{4v}^9 , D_{2d}^9 , D_{2d}^{11} space groups have been determined. Our investigation of $\varepsilon(T)$ in the wide range of temperature (- 170 °C, + 500 °C) discovered the dielectric constant peak at $\approx 30 \text{ °C for Bi}_2\text{NbO}_5\text{F}$ ant at $\approx 10 \text{ °C for Bi}_2\text{TaO}_5\text{F}$. On the single crystals of Bi₂NbO₅F at 15 °C the dielectric hysteresis loop was observed ($P_s = 4 \,\mu \text{coul/cm}^2$). Thus these crystals are also one-layer ferroelectrics with $T_{\rm c} \approx 30$ °C and 10 °C.

References

- [1] ISMAILZADE (I. G.), Kristallografiya, 1963, 8, 852
- [2] ISMAILZADE (I. G.), NESTERENKO (V. I.), MIRISHLI (F. A.) and RUSTAMOV (P. G.), Kristallografiya, 1967, 12, 468.
- [3] ISMAILZADE (I. G.) and MIRISHLI (F. A.), Izv. A. N. S. S. S. S. R., Ser. Fiz., 1969, 33, 1138.
- [4] SUBBARAO (E. C.), J. Amer. Cer. Soc., 1962, 45, 166.
- [5] POPPER (P.), RUDDLESDEN (S. N.) and INGLES (T. A.), *Trans. Brit. Cer.*, Soc., 1957, 56, 356.
- [6] MIRISHLI (F. A.) and ISMAILZADE (I. G.), Kristallografiya, 1969, 14, 933.
- [7] ISMAILZADE (I. G.) and MIRISHLI (F. A.), Izv. A. N. S. S. S. R., Ser. Fiz., 1971.
- [8] GALPERIN (B. L.), YERMAN (L. Ya.), KOLCHIN (I. K.), BELOVA (M. A.) and CHERNYSHEV (G. S.), *Zhurn. Neorg. Chim.*, 1966, 11, 1125.
- [9] ISMAILZADE (I. G.) and MIRISHLI (F. A.), Kristallografiya, 1969, 14, 738.
- [10] WOLFE (R. W.), NEWNAHM (R. E.) and KAY (M. I.), Solid Stat. Communic., 1969, 7, 1797.
- [11] AURIVILLIUS (B.), Arkiv Kemi, 1953, 5, 39.
- [12] MIRISHLI (F. A.), Master Dissertation (Baku, 1971).